

## Dual N-Channel 30 V (D-S) MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
30	0.014 at $V_{GS} = 10$ V	12.1	5.4 nC
	0.017 at $V_{GS} = 4.5$ V	11	

### FEATURES

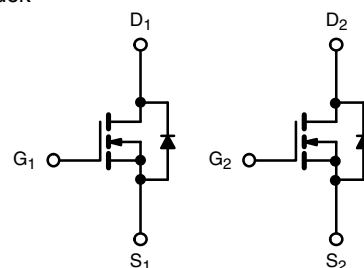
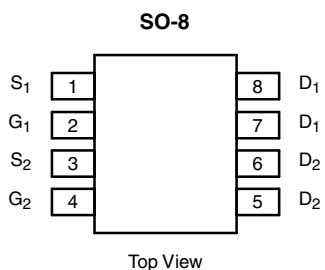
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 %  $R_g$  Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Synchronous Buck
  - Notebooks
  - Servers
  - STB



N-Channel MOSFET    N-Channel MOSFET

**Ordering Information:** Si4202DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ )	$I_D$	$T_C = 25^\circ\text{C}$	A
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Pulsed Drain Current	$I_{DM}$	50	A
Continuous Source Drain Diode Current	$I_S$	$T_C = 25^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
Avalanche Current	$I_{AS}$	15	
Single-Pulse Avalanche Energy	$E_{AS}$	11.25	mJ
Maximum Power Dissipation	$P_D$	$T_C = 25^\circ\text{C}$	W
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	$^\circ\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, c</sup>	$R_{thJA}$	50	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	33	41	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b.  $t = 10$  s.

c. Maximum under steady state conditions is 110  $^\circ\text{C/W}$ .

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA		33		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			- 5.3		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0		2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	20			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8 A		0.0115	0.0140	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5 A		0.0138	0.0170	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 8 A		33		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		710		pF
Output Capacitance	C <sub>oss</sub>			146		
Reverse Transfer Capacitance	C <sub>rss</sub>			63		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8 A		11.2	17	nC
		V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 8 A		5.4	8	
Gate-Source Charge	Q <sub>gs</sub>			1.6		
Gate-Drain Charge	Q <sub>gd</sub>			1.6		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.5	2.5	5	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω		11	22	ns
Rise Time	t <sub>r</sub>			18	35	
Turn-Off Delay Time	t <sub>d(off)</sub>			14	28	
Fall Time	t <sub>f</sub>			8	16	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω		8	16	
Rise Time	t <sub>r</sub>			9	18	
Turn-Off Delay Time	t <sub>d(off)</sub>			17	34	
Fall Time	t <sub>f</sub>			8	16	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			3.1	A
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				50	
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 3 A		0.75	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 5 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		13	26	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			5.5	11	nC
Reverse Recovery Fall Time	t <sub>a</sub>			8		ns
Reverse Recovery Rise Time	t <sub>b</sub>			5		

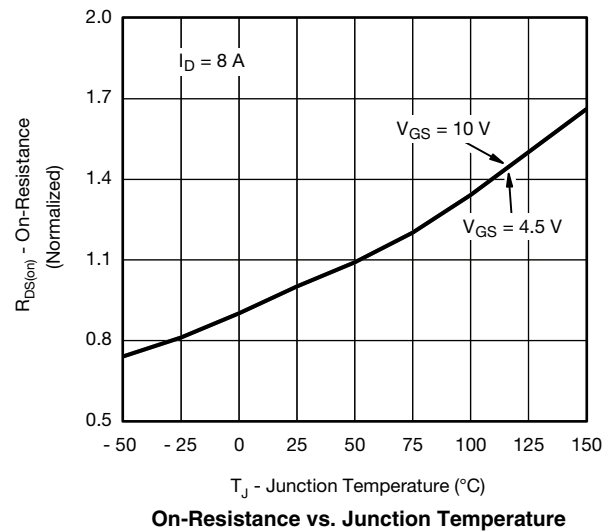
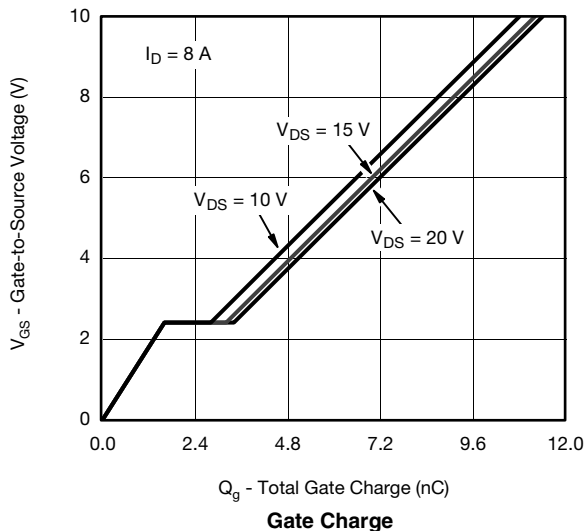
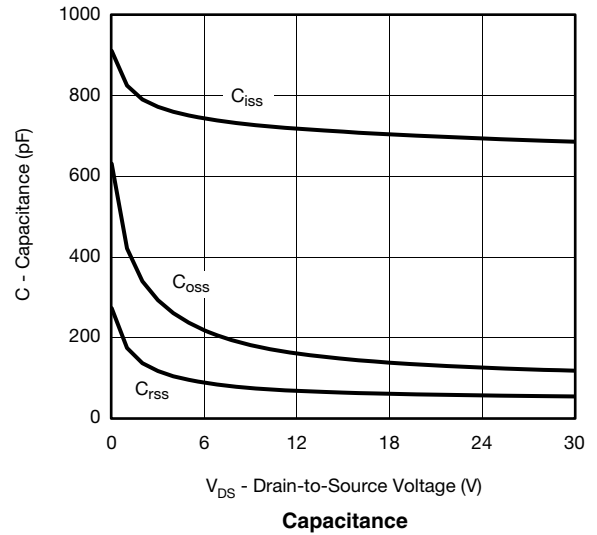
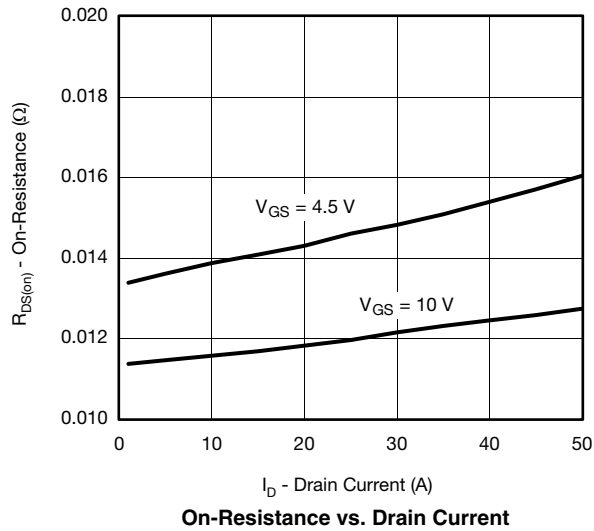
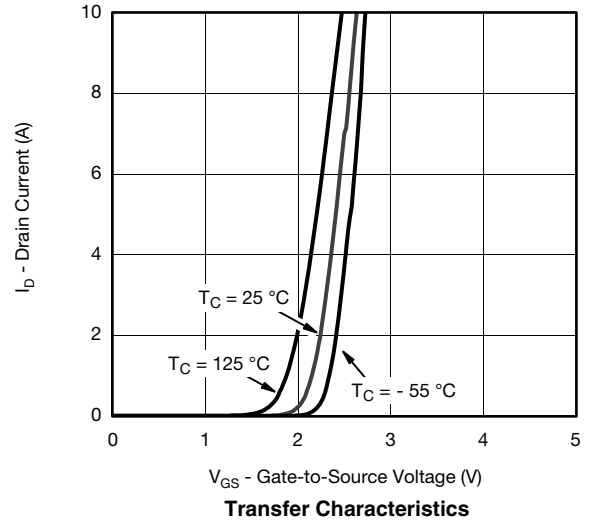
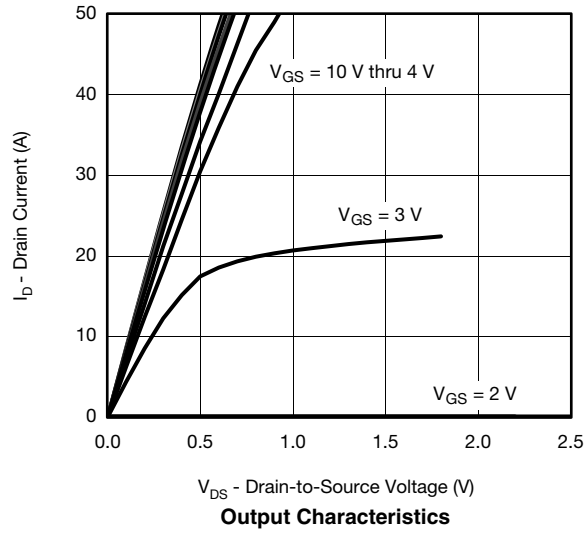
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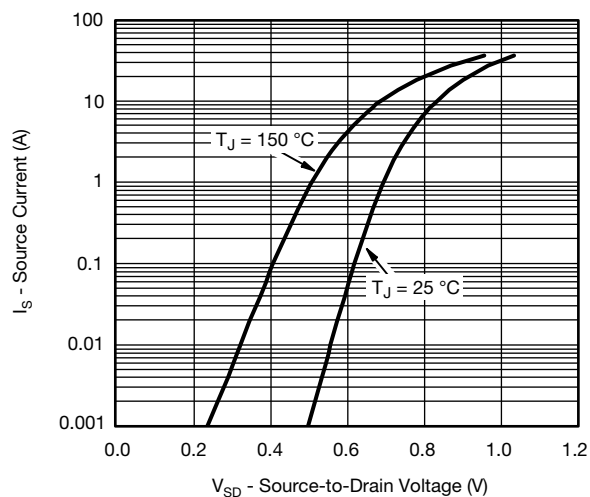
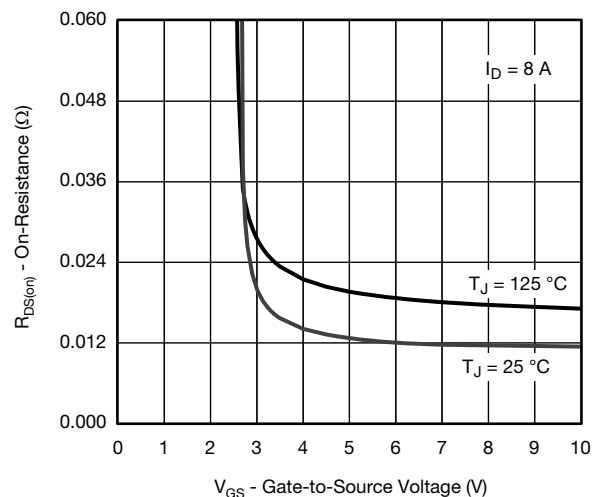
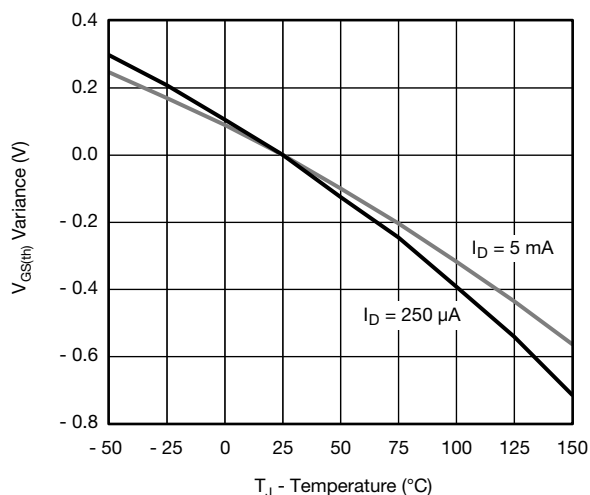
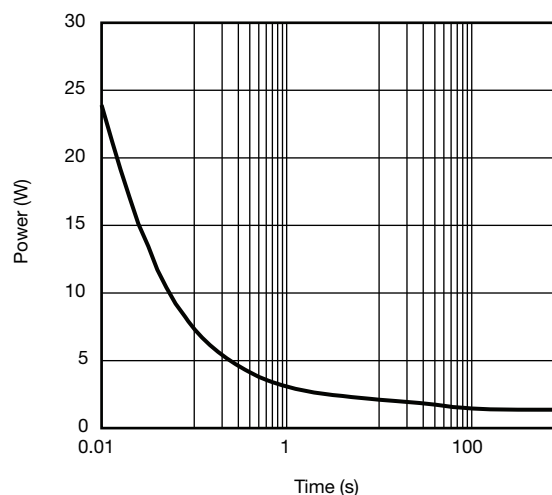
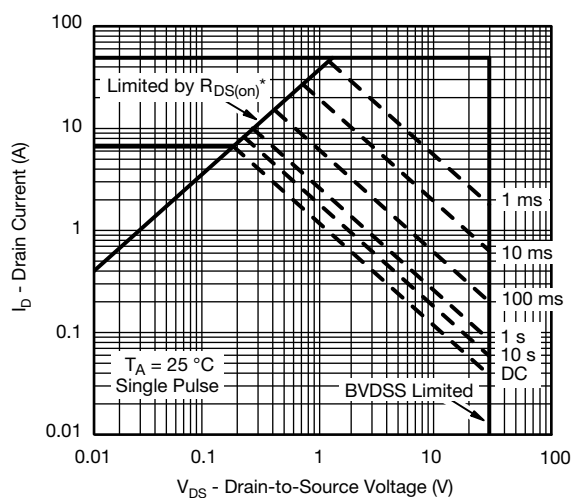
a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

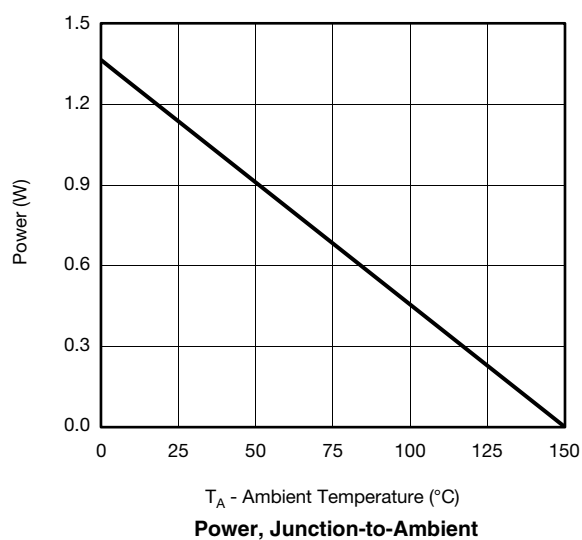
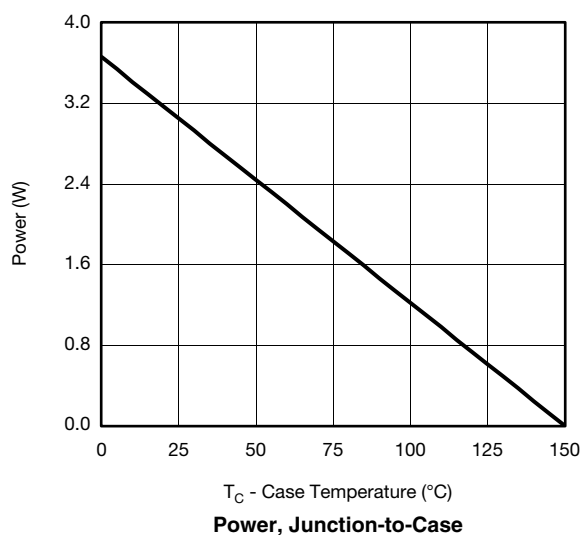
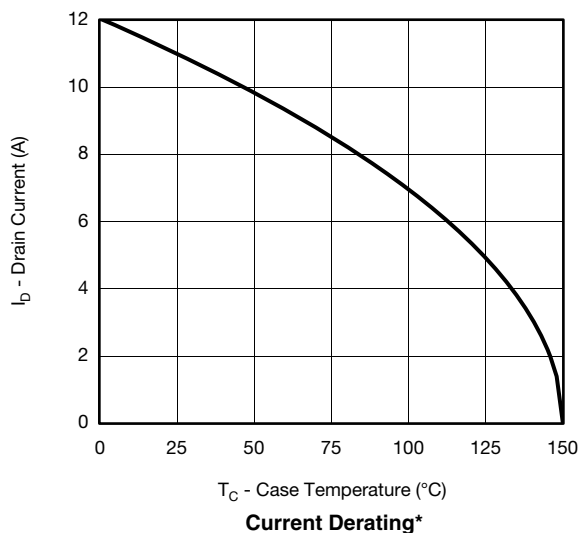
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

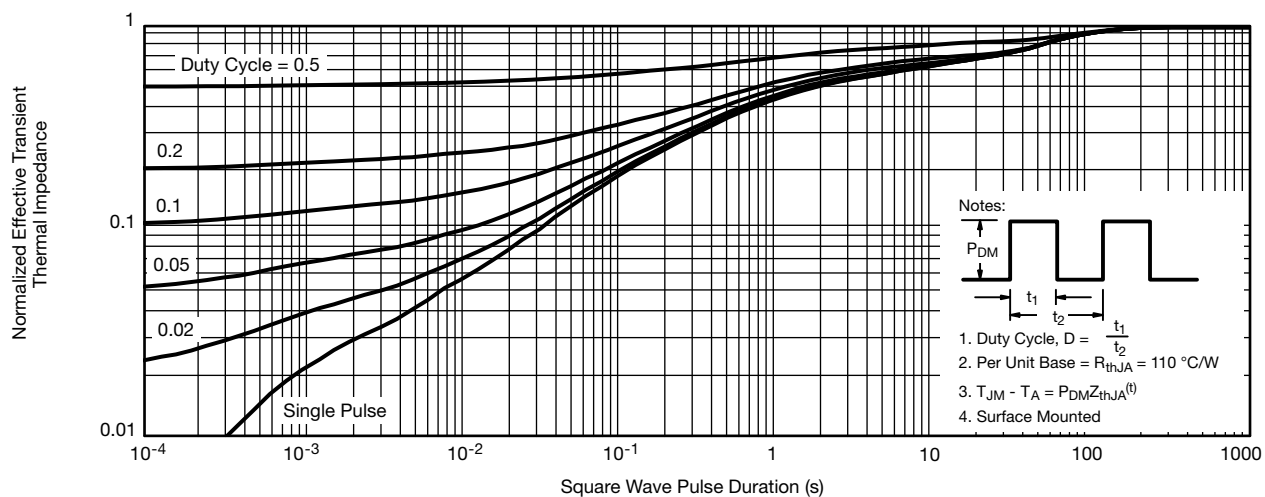
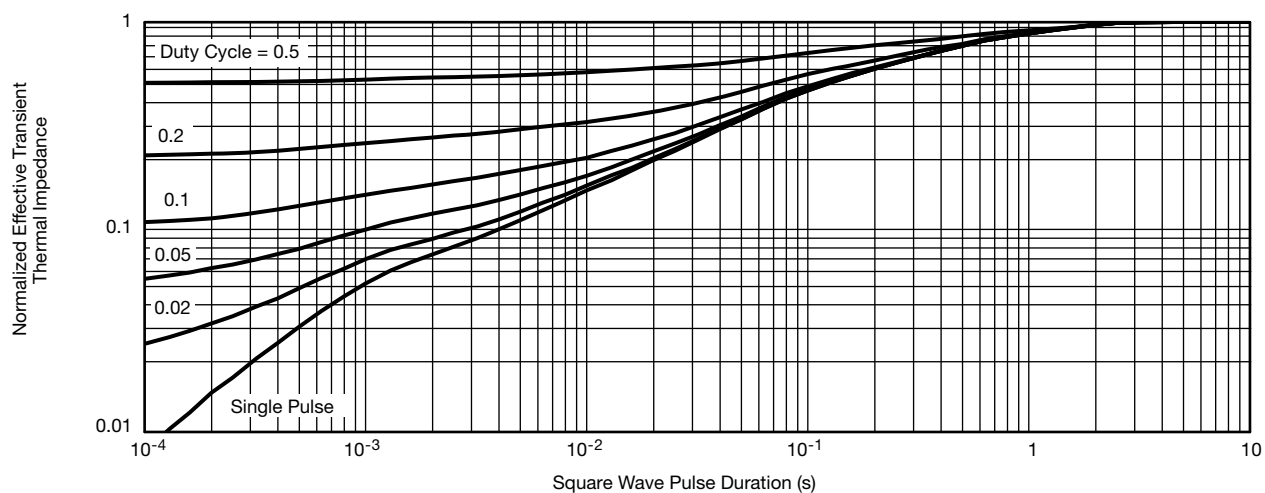


**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient**\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified**Safe Operating Area**

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)





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